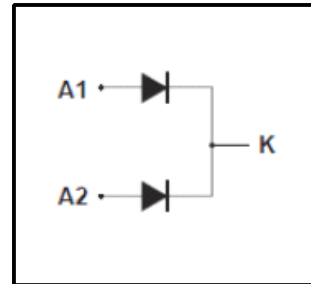


*Silicon Controlled Rectifiers*

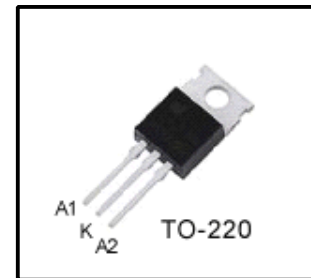
**Features**

- 20A(2×10A),150V
- $V_{F(max)}=0.75V(@T_J=125^{\circ}C)$
- Low power loss,high efficiency
- Common cathode structure
- Guard ring for over voltage protection, High reliability
- Maximum Junction Temperature Range( $175^{\circ}C$ )



**General Description**

Dual center tap Schottky rectifiers suited for High frequency switch power supply and Free wheeling diodes, polarity protection applications.



**Absolute Maximum Ratings**

Symbol	Parameter	Value	Units
$V_{DRM}$	Repetitive Peak reverse Voltage	150	V
$V_{DC}$	Maximum DC blocking Voltage	150	V
$I_{F(RMS)}$	RMS forward Current	20	A
$I_{F(AV)}$	Average forward current	Per diode	10
		Per device	20
$I_{FSM}$	Surge non repetitive forward current	200	A
$I_{RRM}$	Repetitive peak reverse current	1	A
dv/dt	Critical rate of rise of reverse voltage	10000	V/ns
$T_J$	Junction Temperature	175	$^{\circ}C$
$T_{STG}$	Storage Temperature	-40~150	$^{\circ}C$

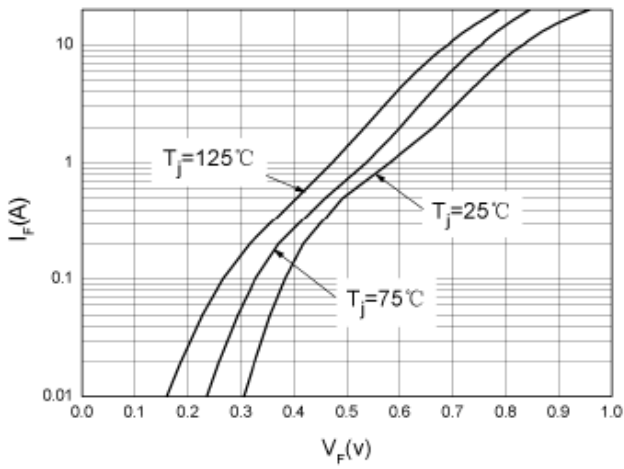
**Thermal Characteristics**

Symbol	Parameter	Value			Units
		Min	Typ	Max	
$R_{QJC}$	Thermal Resistance Junction to Case	-	-	2.2	$^{\circ}C/W$

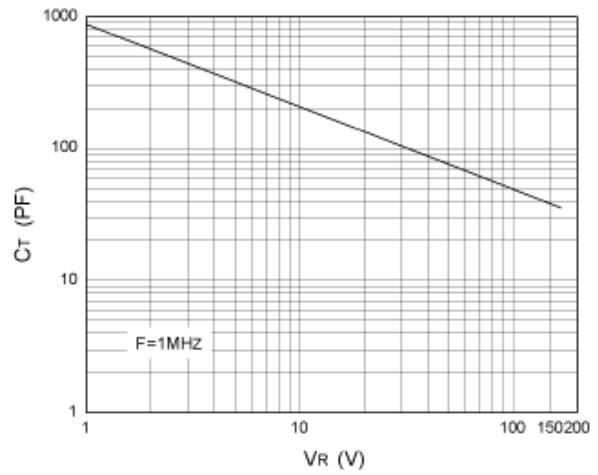
Electrical Characteristics (per diode)

Characteristics	Symbol	Test Conditions		Min	Typ	Max	Units
Reverse leakage current	I <sub>R</sub>	V <sub>R</sub> =V <sub>RRM</sub>	T <sub>j</sub> =25℃	-	-	10	μA
			T <sub>j</sub> =125℃	-	-	5	mA
Forward voltage drop	V <sub>F</sub>	I <sub>F</sub> =10A	T <sub>j</sub> =25℃	-	0.83	0.92	V
			T <sub>j</sub> =125℃	-	0.68	0.75	

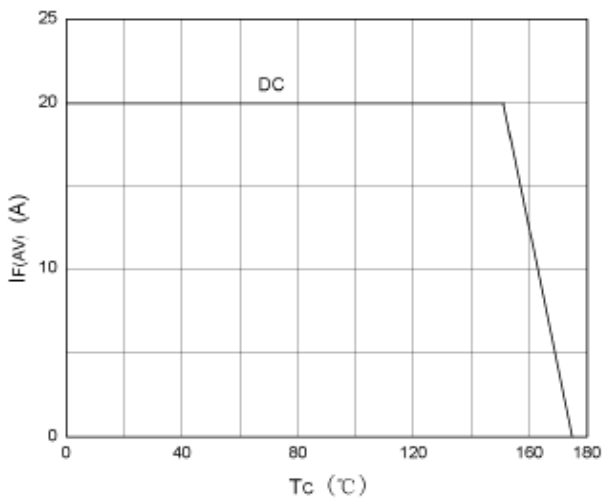
\*Notes:tp =380μs, δ<2%



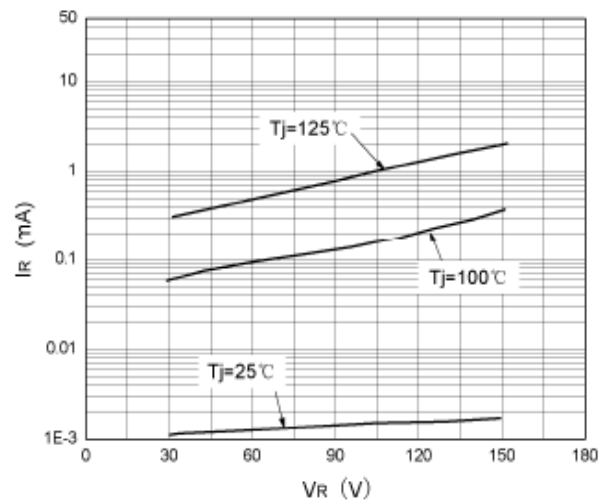
**Fig.1 Forward Voltage Drop Versus Forward current (maximum Values ,per diode)**



**Fig .2 Junction Capacitance Versus reverse Voltage applied (typical Values,per diode)**



**Fig. 3 Average Current versus ambient temperature (d=0.5)(per diode)**



**Fig. 4 Reverse leakage current versus reverse voltage applied ( typical values,per diode)**

**TO-220 Package Dimension**

